L	Hits	Search Text	DB	Time stamp
Number				_
23	1	glue adj layer with thin adj film adj transistor\$3	USPAT; EPO; JPO; DERWENT;	2004/07/18
24	1	glue adj layer same thin adj film adj transistor\$1	IBM_TDB USPAT; EPO; JPO; DERWENT;	2004/07/18
25	63	glue adj layer same transistor\$1	IBM_TDB USPAT; EPO; JPO; DERWENT;	2004/07/18
26	1	etch adj stop same glue adj layer same transistor\$1	IBM_TDB USPAT; EPO; JPO; DERWENT;	2004/07/18
27	623	etch adj stop same (Ti or TiN)	IBM_TDB USPAT; EPO; JPO; DERWENT;	2004/07/18
28	100	etch adj stop near3 (Ti or TiN)	IBM_TDB USPAT; EPO; JPO; DERWENT;	2004/07/18
29	68	etch adj stop near2(Ti or TiN)	IBM_TDB USPAT; EPO; JPO; DERWENT;	2004/07/18
30	30	etch adj stop nearl(Ti or TiN)	IBM_TDB USPAT; EPO; JPO;	2004/07/18
31	208	glue adj layer with TiN	DERWENT; IBM_TDB USPAT; EPO; JPO;	2004/07/18
32	86	glue adj layer near2 TiN	DERWENT; IBM_TDB USPAT; EPO; JPO; DERWENT;	2004/07/18
33	52	glue adj layer nearl TiN	IBM_TDB USPAT; EPO; JPO; DERWENT;	2004/07/18
34	1	glue adj layer near1 TiN same etch adj stop	IBM_TDB USPAT; EPO; JPO; DERWENT;	2004/07/18
-	3	AlNd and AlNdN	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/15
-	44	thin adj film adj transistor\$1 same (neodymium or Nd) same aluminum	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/15
-	281	thin adj film adj transistor\$1 same hydrogenated adj amorphous adj silicon	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/15
-	226	thin adj film adj transistor\$1 same hydrogenated adj amorphous adj silicon	DERWENT; IBM_TDB USPAT; EPO; JPO; DERWENT; IBM TDB	2004/07/18

-	10	thin adj film adj transistor\$1 same	USPAT;	2004/07/18
		hydrogenated adj amorphous adj silicon	EPO; JPO;	13:27
		same advantage\$1	DERWENT;	
			IBM TDB	